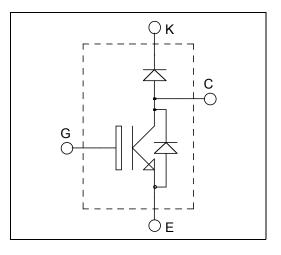


Power Matters."

ISOTOP[®] Boost chopper High speed Trench + Field Stop IGBT4 Power Module

$V_{CES} = 650V$ $I_{C} = 50A$ @ Tc = 80°C





Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction
- Brake switch

Features

- High speed Trench + Field Stop IGBT 4
 - Low voltage drop
 - Low leakage current
 - Low switching losses
- ISOTOP[®] Package (SOT-227)
- Very low stray inductance

Benefits

- Low conduction losses
- Stable temperature behavior
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- RoHS Compliant

All ratings (a) $T_i = 25^{\circ}C$ unless otherwise specified

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V _{CES}	Collector - Emitter Voltage		650	V
т	Continuous Collector Current	$T_C = 25^{\circ}C$	80	
I _C	$T_{\rm C} = 80^{\circ}$		50	Α
I _{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	140	
V _{GE}	Gate – Emitter Voltage		±20	V
P _D	Power Dissipation		220	W

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed



Power Matters."

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 650V$				50	μΑ
V	Collector Emitter Saturation Voltage	$ \begin{array}{c} V_{GE} = 15V & T_{j} = 25^{\circ}C \\ I_{C} = 50A & T_{j} = 150^{\circ}C \end{array} $	$T_j = 25^{\circ}C$	1.4	1.85	2.3	V
V _{CE(sat)}			$T_{j} = 150^{\circ}C$		2.2		v
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 0.8 \text{ mA}$		4.2	5.1	5.6	V
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				150	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$			3100		
C _{oes}	Output Capacitance				116		pF
Cres	Reverse Transfer Capacitance	f = 1 MHz			90		
Q _G	Gate charge	$V_{GE} = 15V, I_C = 50A$ $V_{CE} = 480V$			315		nC
T _{d(on)}	Turn-on Delay Time	Inductive Swite	thing (25°C)		19		
T _r	Rise Time	$V_{GE} = \pm 15V$ $V_{Bus} = 400V$			33		ns
T _{d(off)}	Turn-off Delay Time	$I_C = 50A$			197		115
T _f	Fall Time	$R_G = 7\Omega$			21		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (150°C)			19		
T _r	Rise Time	$V_{GE} = \pm 15V$			29		ns
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 400V$ $I_C = 50A$			227		
T _f	Fall Time	$\frac{R_{\rm C} = 50 \rm{A}}{R_{\rm G} = 7 \Omega}$			22		
Eon	Turn on Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 400V$	$T_j = 150^{\circ}C$		1.2		mJ
E _{off}	Turn off Energy	$I_{\rm C} = 50 \text{A}$ $R_{\rm G} = 7 \Omega$	$T_j = 150^{\circ}C$		1		111,0
I _{sc}	Short Circuit data	$V_{GE} \leq 15V ; V_{Bu}$ $t_p \leq 5\mu s ; T_j = 15$			350		А
R _{thJC}	Junction to Case Thermal Resistance					0.68	°C/W

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Peak Repetitive Reverse Voltage					650	V
I _{RM}	Reverse Leakage Current	$V_R = 650V$				50	μA
I _F	DC Forward Current		$Tc = 25^{\circ}C$		50		Α
V _F	Diode Forward Voltage	$I_F = 50A$	$T_i = 25^{\circ}C$		1.6	2	v
۷F	Diode i of ward Voltage	$V_{GE} = 0V$	$T_{i} = 150^{\circ}C$		1.5		•
t _{rr}	Reverse Recovery Time		$T_j = 25^{\circ}C$		100		ns
۲r	Reverse Recovery Time	1 504	$T_{j} = 150^{\circ}C$		150		115
Q _{rr}	Reverse Recovery Charge	$I_F = 50A$ $V_R = 300V$ $di/dt = 1800A/\mu s$	$T_j = 25^{\circ}C$		2.6		μC
Qrr	Reverse Recovery charge		$T_{j} = 150^{\circ}C$		5.4		μΟ
E _{rr}			$T_j = 25^{\circ}C$		0.6		mJ
LIL	Reverse Recovery Energy		$T_{j} = 150^{\circ}C$		1.2		1115
R _{thJC}	Junction to Case Thermal Resistance					1.14	°C/W

www.microsemi.com

2 - 6



Power Matters."

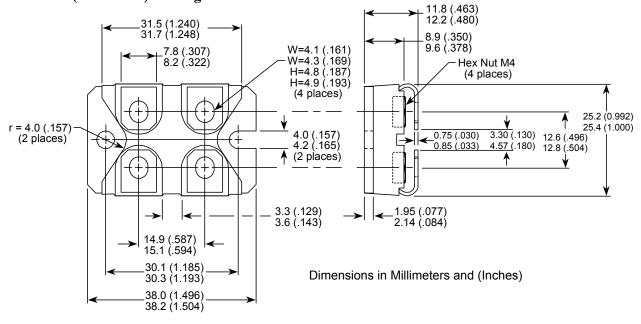
IGBT parallel diode ratings and characteristics

-	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Peak Repetitive Reverse Voltage					650	V
I _{RM}	Reverse Leakage Current	$V_R = 650V$				50	μA
$I_{\rm F}$	DC Forward Current		$Tc = 60^{\circ}C$		20		А
V _F	Diode Forward Voltage	$I_{\rm F} = 20A$ $V_{\rm GE} = 0V$	$T_i = 25^{\circ}C$		1.6	2	V
· 1			$T_{j} = 150^{\circ}C$		1.5		
t _{rr}	Reverse Recovery Time		$T_j = 25^{\circ}C$		100		ns
۹r	Reverse Receivery Time	x 20.4	$T_{j} = 150^{\circ}C$		150		115
Q _{rr}	Reverse Recovery Charge	$V_{\rm R} = 300 V$	$T_j = 25^{\circ}C$		1.1		μC
Qrr	Reverse Recovery Charge		$T_{j} = 150^{\circ}C$		2.3		μĊ
Err	Reverse Recovery Energy		$T_j = 25^{\circ}C$		0.23		mJ
			$T_{j} = 150^{\circ}C$		0.50		1115
R _{thJC}	Junction to Case Thermal Resistance					2.6	°C/W

Thermal and package characteristics

Symbol	Characteristic	Min	Тур	Max	Unit
VISOL	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz	2500			V
T_J, T_{STG}	Storage Temperature Range	-55		175	
T_{JOP}	Recommended junction temperature under switching conditions	-55		T _J max -25	°C
T _L	Max Lead Temp for Soldering:0.063" from case for 10 sec			300	
Torque	Mounting torque (Mounting = 8-32 or 4mm Machine and terminals = 4mm Machine)			1.5	N.m
Wt	Package Weight		29.2		g

SOT-227 (ISOTOP[®]) Package Outline



ISOTOP® is a registered trademark of ST Microelectronics NV

www.microsemi.com

3 - 6



Output Characteristics

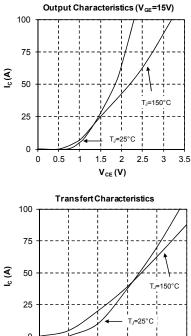
100

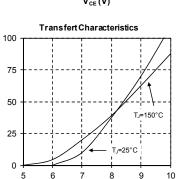
75

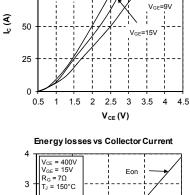
T_J = 150°C

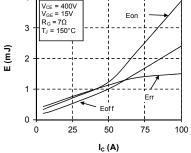
Power Matters."





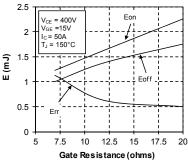




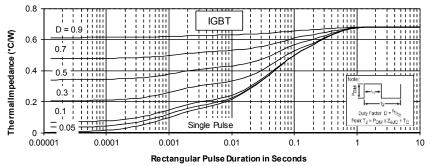


Switching EnergyLosses vs Gate Resistance

 $V_{GE}(V)$

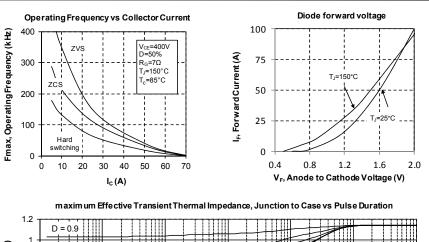


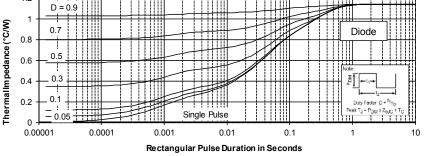
maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration



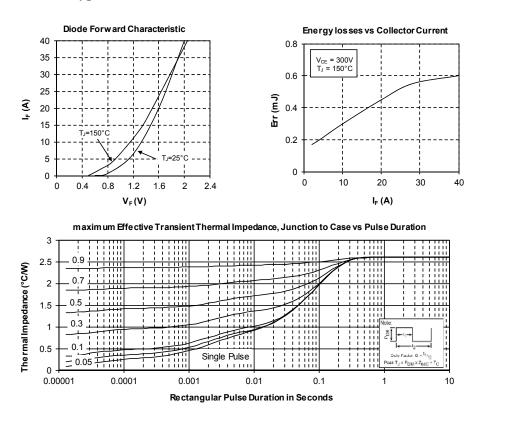
www.microsemi.com







IGBT parallel diode Typical Performance Curves



www.microsemi.com

APT50GLQ65JU2 - Rev 0 August, 2016



Power Matters."

DISCLAIMER

The information contained in the document (unless it is publicly available on the Web without access restrictions) is PROPRIETARY AND CONFIDENTIAL information of Microsemi and cannot be copied, published, uploaded, posted, transmitted, distributed or disclosed or used without the express duly signed written consent of Microsemi. If the recipient of this document has entered into a disclosure agreement with Microsemi, then the terms of such Agreement will also apply. This document and the information contained herein may not be modified, by any person other than authorized personnel of Microsemi. No license under any patent, copyright, trade secret or other intellectual property right is granted to or conferred upon you by disclosure or delivery of the information, either expressly, by implication, inducement, estoppels or otherwise. Any license under such intellectual property rights must be approved by Microsemi in writing signed by an officer of Microsemi.

Microsemi reserves the right to change the configuration, functionality and performance of its products at anytime without any notice. This product has been subject to limited testing and should not be used in conjunction with lifesupport or other mission-critical equipment or applications. Microsemi assumes no liability whatsoever, and Microsemi disclaims any express or implied warranty, relating to sale and/or use of Microsemi products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright or other intellectual property right. Any performance specifications believed to be reliable but are not verified and customer or user must conduct and complete all performance and other testing of this product as well as any user or customers final application. User or customer shall not rely on any data and performance specifications or parameters provided by Microsemi. It is the customer's and user's responsibility to independently determine suitability of any Microsemi product and to test and verify the same. The information contained herein is provided "AS IS, WHERE IS" and with all faults, and the entire risk associated with such information is entirely with the User. Microsemi specifically disclaims any liability of any kind including for consequential, incidental and punitive damages as well as lost profit. The product is subject to other terms and conditions which can be located on the web at http://www.microsemi.com/legal/tnc.asp

Life Support Application

Seller's Products are not designed, intended, or authorized for use as components in systems intended for space, aviation, surgical implant into the body, in other applications intended to support or sustain life, or for any other application in which the failure of the Seller's Product could create a situation where personal injury, death or property damage or loss may occur (collectively "Life Support Applications").

Buyer agrees not to use Products in any Life Support Applications and to the extent it does it shall conduct extensive testing of the Product in such applications and further agrees to indemnify and hold Seller, and its officers, employees, subsidiaries, affiliates, agents, sales representatives and distributors harmless against all claims, costs, damages and expenses, and attorneys' fees and costs arising, directly or directly, out of any claims of personal injury, death, damage or otherwise associated with the use of the goods in Life Support Applications, even if such claim includes allegations that Seller was negligent regarding the design or manufacture of the goods.

Buyer must notify Seller in writing before using Seller's Products in Life Support Applications. Seller will study with Buyer alternative solutions to meet Buyer application specification based on Sellers sales conditions applicable for the new proposed specific part.